

### 100V PNP LOW SATURATION MEDIUM POWER TRANSISTOR

### **Features**

- BV<sub>CEO</sub> > -100V
- I<sub>C</sub> = -5A Continuous Collector Current
- I<sub>CM</sub> = -10A Peak Collector Current
- R<sub>SAT</sub> = 67mΩ Typical for Low Equivalent On Resistance
- Low Saturation Voltage
- High Gain Hold-Up (100 min @ 1A)
- Lead-Free Finish; RoHS Compliant (Note 1 & 2)
- Halogen and Antimony Free. "Green" Device (Note 3)
- Qualified to AEC-Q101 Standards for High Reliability

### **Mechanical Data**

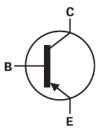
- Case: TO252 (DPAK)
- Case Material: Molded Plastic, "Green" Molding Compound;
   UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish Matte Tin; Solderable per MIL-STD-202, Method 208 (3)
- Weight: 0.34 grams (Approximate)

## **Application**

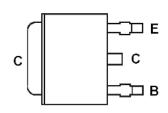
- DC-DC Converters
- Power Switches
- Motor Control
- Automotive Circuits
- Inverter Circuits







**Device Schematic** 



Pin Out Configuration Top view

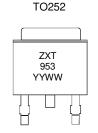
## Ordering Information (Note 4)

Product	Compliance	Marking	Reel size (inches)	Tape width (mm)	Quantity per reel
ZXT953KTC	AEC-Q101	ZXT953	13	16	2,500

Notes:

- 1. EU Directive 2002/95/EC (RoHS) & 2011/65/EU (RoHS 2) compliant. All applicable RoHS exemptions applied.
- 2. See http://www.diodes.com/quality/lead\_free.html for more information about Diodes Incorporated's definitions of Halogen- and Antimony-free, "Green" and Lead-free.
- 3. Halogen- and Antimony-free "Green" products are defined as those which contain <900ppm bromine, <900ppm chlorine (<1500ppm total Br + Cl) and <1000ppm antimony compounds.
- 4. For packaging details, go to our website at http:///www.diodes.com/products/packages.html.

## **Marking Information**



ZXT953 = Product Type Marking Code YYWW = Date Code Marking YY = Last Digit of Year (ex: 15 = 2015) WW = Week Code (01 - 53)



# Absolute Maximum Ratings (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	BV <sub>CBO</sub>	-140	V
Collector-Base Voltage	BV <sub>CER</sub>	-140	V
Collector-Emitter Voltage	$V_{CEO}$	-100	V
Emitter-Base Voltage	$V_{EBO}$	-7	V
Continuous Collector Current	Ic	-5	Α
Base Current	Ι <sub>Β</sub>	-0.5	A
Peak Pulse Collector Current	I <sub>CM</sub>	-10	A

## Thermal Characteristics (@TA = +25°C, unless otherwise specified.)

Characteristic	Symbol	Value	Unit		
	(Note 5)		2.1		
Power Dissipation	(Note 6)	P <sub>D</sub>	3.2	W	
	(Note 7)		4.2		
	(Note 5)		59		
Thermal Resistance, Junction to Ambient Air	(Note 6)	$R_{\thetaJA}$	39	°C/W	
	(Note 7)		30		
Thermal Resistance, Junction to Leads	(Note 8)	$R_{ heta JL}$	1.8	°C/W	
Operating and Storage Temperature Range	$T_{J,}T_{STG}$	-55 to +150	°C		

# ESD Ratings (Note 9)

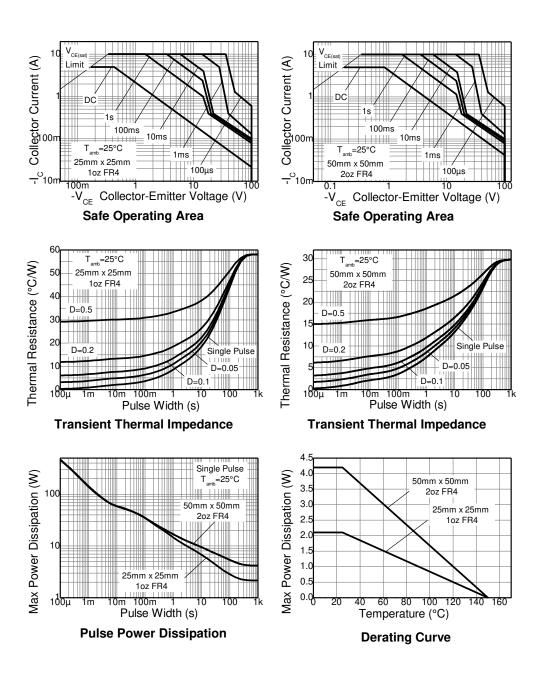
Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	4,000	V	3A
Electrostatic Discharge - Machine Model	ESD MM	400	V	С

Notes:

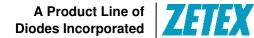
- 5. For a device mounted with the exposed collector pad on 25mm x 25mm 1oz copper that is on a single-sided 1.6mm FR4 PCB; device is measured under still air conditions whilst operating in a steady-state.
- 6. Same as Note 5, except the device is mounted on 50mm x 50mm with 1oz copper.
- 7. Same as Note 5, except the device is mounted on 50mm x 50mm with 2oz copper.
- 8. Thermal resistance from junction to solder-point (at the end of the collector lead).
- 9. Refer to JEDEC specification JESD22-A114 and JESD22-A115.



# **Thermal Characteristics and Derating Information**









# Electrical Characteristics (@T<sub>A</sub> = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Тур.	Max	Unit	Test Condition
Collector-Base Breakdown Voltage	$BV_CBO$	-140	-170	-	V	$I_C = -100 \mu A$
Collector-Base Breakdown Voltage	BV <sub>CER</sub>	-140	-170	-	V	$I_C = -1\mu A, R_{BE} \le 1k\Omega$
Collector-Emitter Breakdown Voltage (Note 10)	BV <sub>CEO</sub>	-100	-125	-	V	$I_C = -10mA$
Emitter-Base Breakdown Voltage	$BV_{EBO}$	-7	-8.1	-	V	$I_E = -100\mu A$
Collector Cut-Off Current	I <sub>CBO</sub>	-	<1	-20	nA	$V_{CB} = -100V$
Emitter Cut-Off Current	I <sub>EBO</sub>	-	<1	-10	nA	$V_{EB} = -6V$
Emitter Cut-Off Current	I <sub>CER</sub>	-	<1	-20	nA	$V_{CE} = -100V$ , $R_{BE} \le 1k\Omega$
DC Current Transfer Static Ratio (Note 10)	h <sub>FE</sub>	100 100 50 15	220 200 85 30	- 300 - -	-	$I_{C} = -10 \text{mA}, V_{CE} = -1 \text{V}$ $I_{C} = -1 \text{A}, V_{CE} = -1 \text{V}$ $I_{C} = -3 \text{A}, V_{CE} = -1 \text{V}$ $I_{C} = -5 \text{A}, V_{CE} = -1 \text{V}$
Collector-Emitter Saturation Voltage (Note 10)	V <sub>CE(sat)</sub>	- - -	-20 -80 -140 -335	-30 -100 -175 -390	mV	I <sub>C</sub> = -0.1A, I <sub>B</sub> = -10mA I <sub>C</sub> = -1A, I <sub>B</sub> = -100mA I <sub>C</sub> = -2A, I <sub>B</sub> = -200mA I <sub>C</sub> = -5A, I <sub>B</sub> = -500mA
Base-Emitter Saturation Voltage (Note 10)	V <sub>BE(sat)</sub>	-	-1.01	-1.1	V	$I_C = -5A$ , $I_B = -500mA$
Base-Emitter Turn-On Voltage (Note 10)	V <sub>BE(on)</sub>	-	-0.94	-1.05	V	$I_C = -5A$ , $V_{CE} = -1V$
Transitional Frequency	f <sub>T</sub>	-	125	-	MHz	I <sub>C</sub> = -100mA, V <sub>CE</sub> = -10V f = 50MHz
Output Capacitance	C <sub>OBO</sub>	-	65	-	pF	$V_{CB} = -10V$ , $f = 1MHz$ ,
Switching Times	ton toff	-	110 460	-	nS	$I_{C} = -2A$ , $V_{CC} = -10V$ , $I_{B1} = I_{B2} = -200mA$

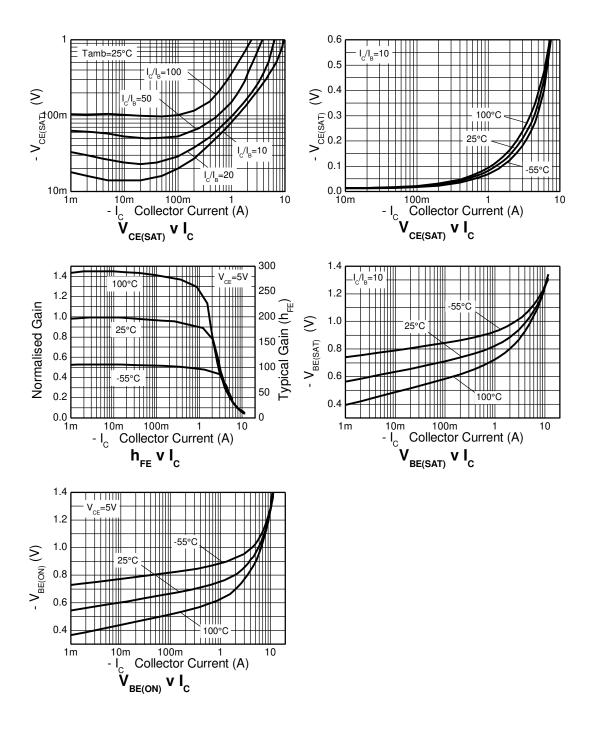
Note:

10. Measured under pulsed conditions. Pulse width  $\leq$  300 $\mu$ s. Duty cycle  $\leq$ 2%.





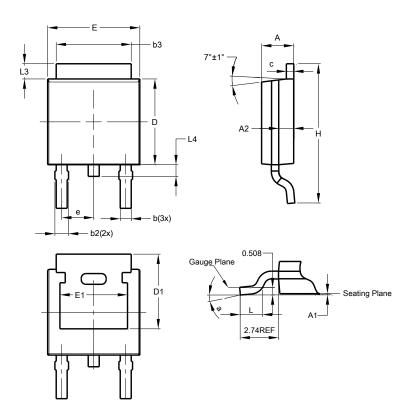
# Typical Electrical Characteristics (@TA = +25°C, unless otherwise specified.)





# **Package Outline Dimensions**

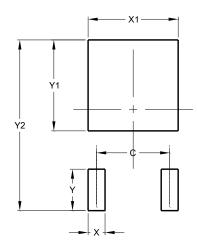
Please see AP02002 at http://www.diodes.com/datasheets/ap02002.pdf for the latest version.



TO252 (DPAK)				
Dim	Min	Max	Тур	
Α	2.19	2.39	2.29	
<b>A</b> 1	0.00	0.13	0.08	
A2	0.97	1.17	1.07	
q	0.64	0.88	0.783	
b2	0.76	1.14	0.95	
b3	5.21	5.46	5.33	
С	0.45	0.58	0.531	
D	6.00	6.20	6.10	
D1	5.21	-	-	
е	-	-	2.286	
Е	6.45	6.70	6.58	
E1	4.32	-	-	
Н	9.40	10.41	9.91	
L	1.40	1.78	1.59	
L3	0.88	1.27	1.08	
L4	0.64	1.02	0.83	
а	0°	10°	-	
All Dimensions in mm				

# **Suggested Pad Layout**

Please see AP02001 at http://www.diodes.com/datasheets/ap02001.pdf for the latest version.



Dimensions	Value (in mm)
С	4.572
X	1.060
X1	5.632
Υ	2.600
Y1	5.700
Y2	10.700

For high voltage applications, the appropriate industry sector guidelines should be considered with regards to creepage and clearance distances between device terminals and PCB tracking.





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